

Substitute Form PTO-1449
(Modified)U.S. Department of Commerce
Patent and Trademark OfficeAttorney Docket No.
07977-0093002Application No.
09/379,702**CORRECTED Information Disclosure Statement
by Applicant**

(Use several sheets if necessary)

(37 CFR §1.98(b))

Applicant
Hisashi Ohtani et al.Filing Date
August 24, 1999Group Art Unit
2815**U.S. Patent Documents**

Examiner Initial	Desig. ID	Document Number	Publication Date	Patentee	Class	Subclass	Filing Date If Appropriate
	A.	5,147,826	09/15/1992	Liu et al.			
	B.	5,529,937	06/25/1996	Zhang et al.			
	C.	5,569,610	10/29/1996	Zhang et al.			
	D.	5,621,224	10/05/1995	Yamazaki et al.			
	E.	5,693,541	12/02/1997	Yamazaki et al.			
	F.	5,744,824	06/02/1995	Kousai et al.			
	G.	5,756,364	11/22/1995	Tanaka et al.			
	H.	5,817,549	08/30/1995	Zhang et al.			

Foreign Patent Documents or Published Foreign Patent Applications

Examiner Initial	Desig. ID	Document Number	Publication Date	Country or Patent Office	Class	Subclass	Translation	
							Yes	No
	I.							
	J.							
	K.							
	L.							

Other Documents (include Author, Title, Date, and Place of Publication)

Examiner Initial	Desig. ID	Document
	M.	Kawazu, Japanese Journal of Applied Physics: vol. 29 no. 4 April 1990 pgs:2698-2704 "Low-Temperature Crystallization of Hydrogenated Amorphous Silicon Induced by Nickel Silicide Formation"
	N.	Kawazu, Japanese Journal of Applied Physics: vol. 29 no. 4 April 1990 pgs:729-738 "Initial Stage of the Interfacial Reaction between Nickel and Hydrogenated Amorphous Silicon"
	O.	Hayzelden, Journal of Applied Physics: 73 (12), 15 June 1993 pgs:8279-8289 "Silicide Formation and Silicide-Mediated Crystallization of Nickel Implanted Amorphous Silicon Thin Films"
	P.	Kuo, The Electrochemical Society Proceedings: vol.94-35 pgs:116-122 "Thin Film Technologies"
	Q.	Liu, Applied Physics Letters 55(7) 14 Aug. 1989 pgs: 660-662 "Selective area crystallization of amorphous silicon films by low-temperature rapid thermal annealing"
	R.	Cuane, Applied Surface Science 36 (1989) pgs: 597-604 "Combined CW Laser and Furnace annealing of Amorphous Si and Ge in Contact with Some Metals"
	S.	Wolf, Silicon Processing for the VLSI Era, Vol.2 1986 pgs: 273-275 "Passivation Layers"

Examiner Signature	/Eugene Lee/	Date Considered
05/09/2009		
EXAMINER: Initials citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.		

ALL REFERENCES CONSIDERED EXCEPT WHERE LINED THROUGH. /E.L./

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	AB.						
	AC.						
	AD.						
	AE.						
	AF.						
	AG.						
	AH.						
	AI.						
	AJ.						
	AK.						

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							Yes	No
	AL.	7-235491	09/05/1995	Japan			ABS	
	AM.							
	AN.							
	AO.							
	AP.							

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	AS.		
	AT.		

Examiner Signature <i>/Eugene Lee/</i>	Date Considered 05/09/2009
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